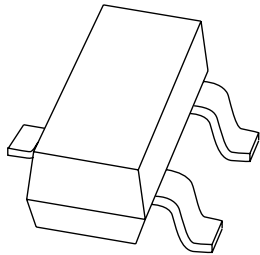


DATA SHEET



BC849; BC850 NPN general purpose transistors

Product data sheet
Supersedes data of 1999 Apr 08

2004 Jan 16



NPN general purpose transistors

BC849; BC850

FEATURES

- Low current (max. 100 mA)
- Low voltage (max. 45 V).

APPLICATIONS

- General purpose switching and amplification.

DESCRIPTION

NPN transistor in a SOT23 plastic package.
PNP complements: BC859 and BC860.

MARKING

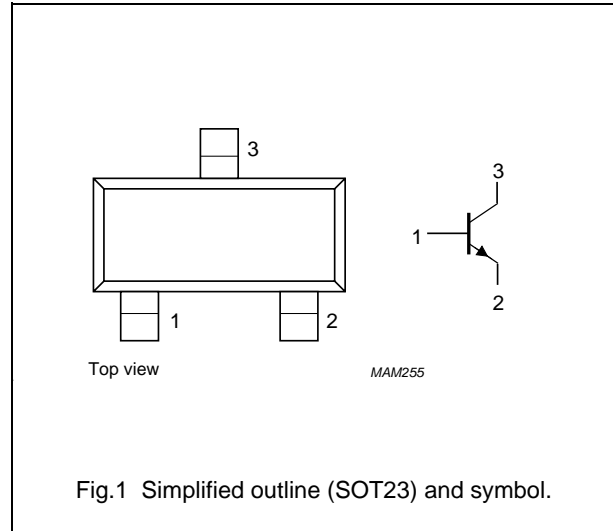
| TYPE NUMBER | MARKING CODE ⁽¹⁾ | TYPE NUMBER | MARKING CODE ⁽¹⁾ |
|-------------|-----------------------------|-------------|-----------------------------|
| BC849B | 2B* | BC850B | 2F* |
| BC849C | 2C* | BC850C | 2G* |

Note

- * = p : Made in Hong Kong.
* = t : Made in Malaysia.
* = W : Made in China.

PINNING

| PIN | DESCRIPTION |
|-----|-------------|
| 1 | base |
| 2 | emitter |
| 3 | collector |



ORDERING INFORMATION

| TYPE NUMBER | PACKAGE | | |
|-------------|---------|--|---------|
| | NAME | DESCRIPTION | VERSION |
| BC849B | - | plastic surface mounted package; 3 leads | SOT23 |
| BC849C | | | |
| BC850B | | | |
| BC850C | | | |

NPN general purpose transistors

BC849; BC850

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

| SYMBOL | PARAMETER | CONDITIONS | MIN. | MAX. | UNIT |
|------------------|-------------------------------|----------------------------------|------|------|------|
| V _{CBO} | collector-base voltage | open emitter | – | 30 | V |
| | BC849 | | | 50 | V |
| V _{CEO} | collector-emitter voltage | open base | – | 30 | V |
| | BC850 | | | 45 | V |
| V _{EBO} | emitter-base voltage | open collector | – | 5 | V |
| I _C | collector current (DC) | | – | 100 | mA |
| I _{CM} | peak collector current | | – | 200 | mA |
| I _{BM} | peak base current | | – | 200 | mA |
| P _{tot} | total power dissipation | T _{amb} ≤ 25 °C; note 1 | – | 250 | mW |
| T _{stg} | storage temperature | | –65 | +150 | °C |
| T _j | junction temperature | | – | 150 | °C |
| T _{amb} | operating ambient temperature | | –65 | +150 | °C |

Note

1. Transistor mounted on an FR4 printed-circuit board.

THERMAL CHARACTERISTICS

| SYMBOL | PARAMETER | CONDITIONS | VALUE | UNIT |
|----------------------|---|------------|-------|------|
| R _{th(j-a)} | thermal resistance from junction to ambient | note 1 | 500 | K/W |

Note

1. Transistor mounted on an FR4 printed-circuit board.

NPN general purpose transistors

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

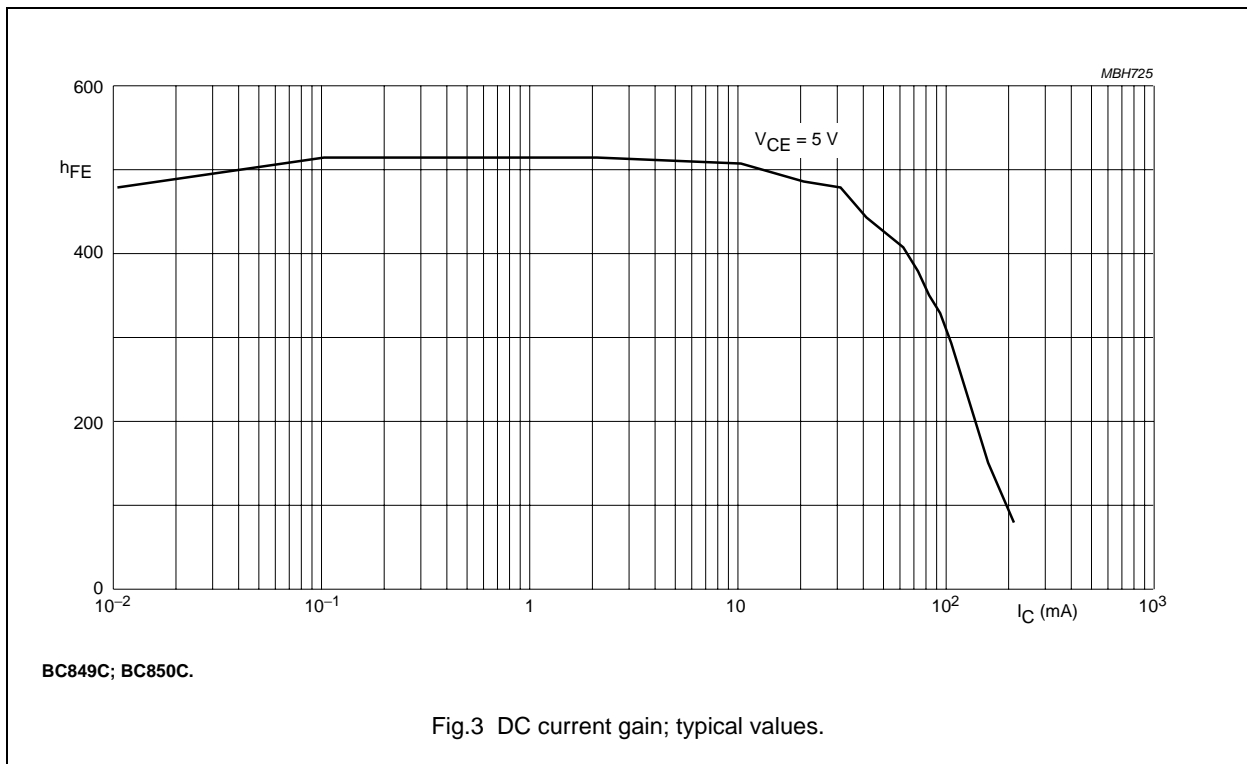
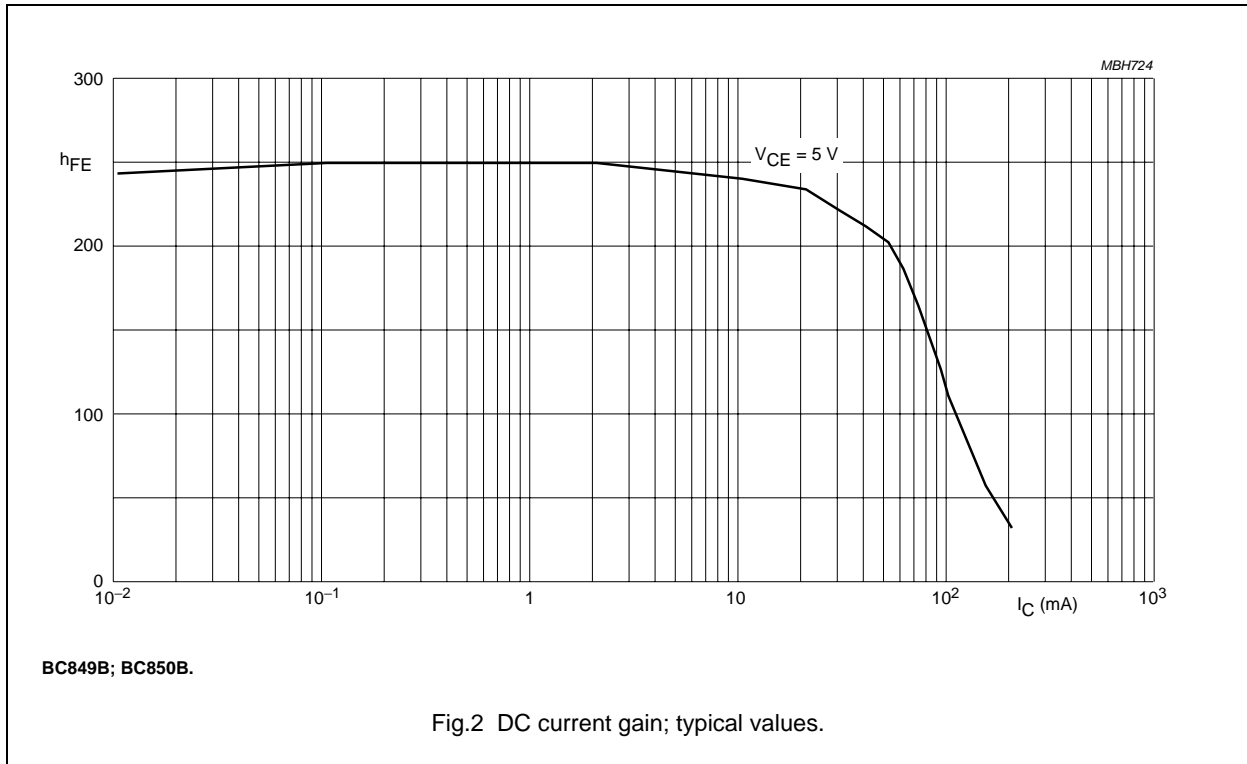
| SYMBOL | PARAMETER | CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|-------------|--------------------------------------|---|------|------|------|---------------|
| I_{CBO} | collector cut-off current | $I_E = 0; V_{CB} = 30\text{ V}$ | – | – | 15 | nA |
| | | $I_E = 0; V_{CB} = 30\text{ V}; T_j = 150\text{ °C}$ | – | – | 5 | μA |
| I_{EBO} | emitter cut-off current | $I_C = 0; V_{EB} = 5\text{ V}$ | – | – | 100 | nA |
| h_{FE} | DC current gain BC849B; BC850B | $I_C = 10\text{ }\mu\text{A}; V_{CE} = 5\text{ V};$ see Figs 2 and 3 | – | 240 | – | |
| | BC849C; BC850C | | – | 450 | – | |
| h_{FE} | DC current gain BC849B; BC850B | $I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ see Figs 2 and 3 | 200 | 290 | 450 | |
| | BC849C; BC850C | | 420 | 520 | 800 | |
| V_{CEsat} | collector-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$ | – | 90 | 250 | mV |
| | | $I_C = 100\text{ mA}; I_B = 5\text{ mA}$ | – | 200 | 600 | mV |
| V_{BEsat} | base-emitter saturation voltage | $I_C = 10\text{ mA}; I_B = 0.5\text{ mA};$ note 1 | – | 700 | – | mV |
| | | $I_C = 100\text{ mA}; I_B = 5\text{ mA};$ note 1 | – | 900 | – | mV |
| V_{BE} | base-emitter voltage | $I_C = 2\text{ mA}; V_{CE} = 5\text{ V};$ note 2 | 580 | 660 | 700 | mV |
| | | $I_C = 10\text{ mA}; V_{CE} = 5\text{ V};$ note 2 | – | – | 770 | mV |
| C_C | collector capacitance | $I_E = i_e = 0; V_{CB} = 10\text{ V}; f = 1\text{ MHz}$ | – | 2.5 | – | pF |
| C_e | emitter capacitance | $I_C = i_c = 0; V_{EB} = 500\text{ mV}; f = 1\text{ MHz}$ | – | 11 | – | pF |
| f_T | transition frequency | $I_C = 10\text{ mA}; V_{CE} = 5\text{ V}; f = 100\text{ MHz}$ | 100 | – | – | MHz |
| F | noise figure | $I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 10\text{ Hz to }15.7\text{ kHz}$ | – | – | 4 | dB |
| | | $I_C = 200\text{ }\mu\text{A}; V_{CE} = 5\text{ V}; R_S = 2\text{ k}\Omega;$ $f = 1\text{ kHz}; B = 200\text{ Hz}$ | – | – | 4 | dB |

Notes

- V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.
- V_{BE} decreases by about 2 mV/K with increasing temperature.

NPN general purpose transistors

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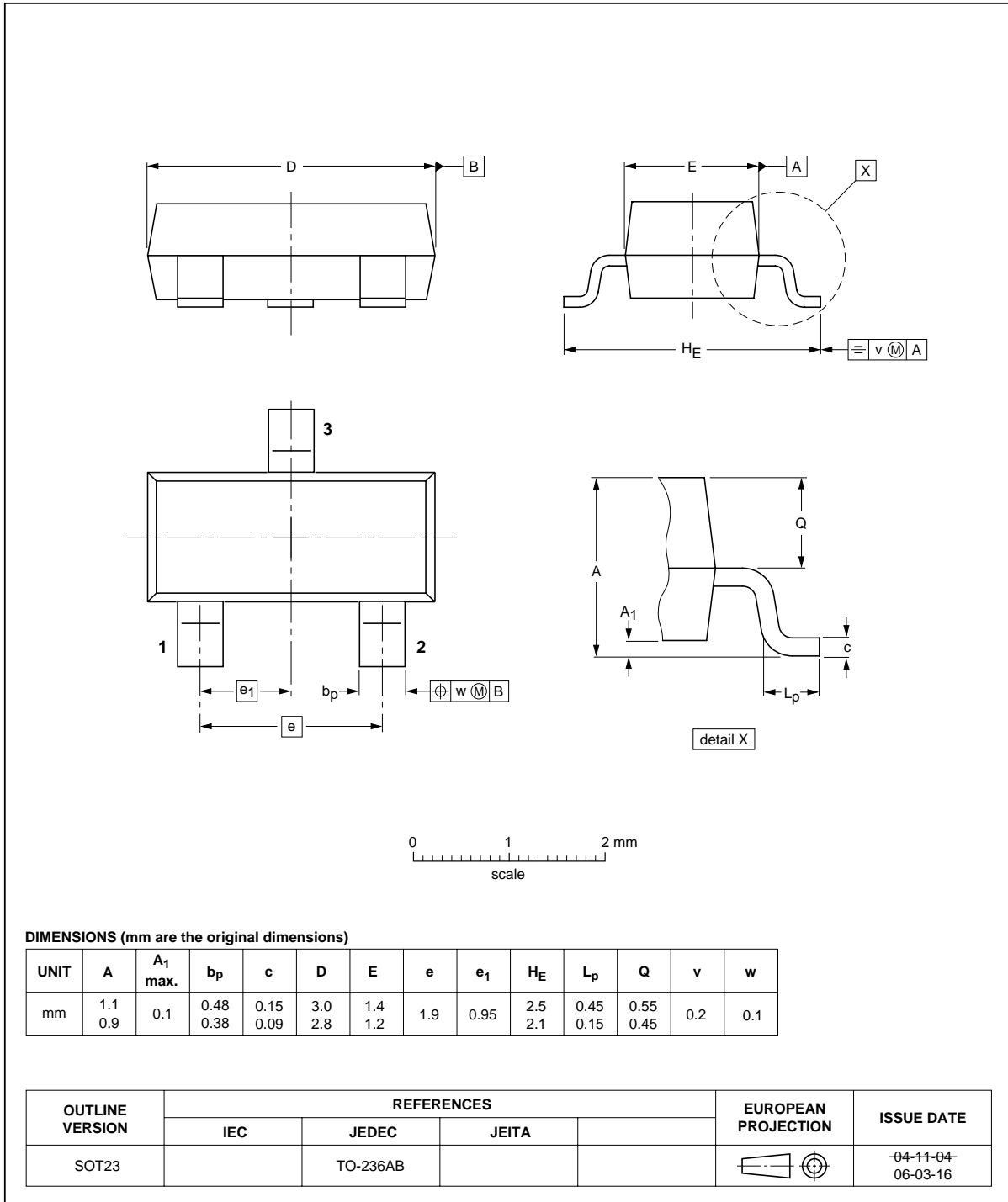
NPN general purpose transistors

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PACKAGE OUTLINE

Plastic surface-mounted package; 3 leads

SOT23



NPN general purpose transistors

BC849; BC850

DATA SHEET STATUS

| DOCUMENT STATUS ⁽¹⁾ | PRODUCT STATUS ⁽²⁾ | DEFINITION |
|--------------------------------|-------------------------------|---|
| Objective data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary data sheet | Qualification | This document contains data from the preliminary specification. |
| Product data sheet | Production | This document contains the product specification. |

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Customer notification

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Contact information

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